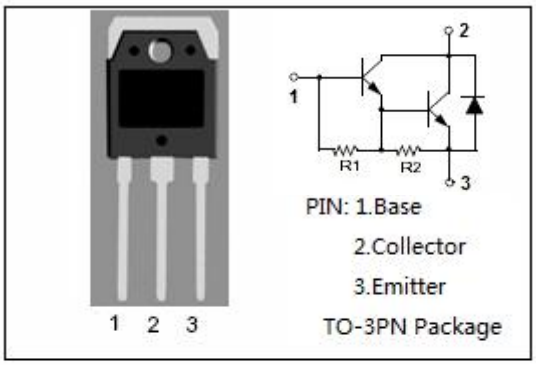
isc Silicon NPN Darlington Power Transistor 2SD1522



DESCRIPTION

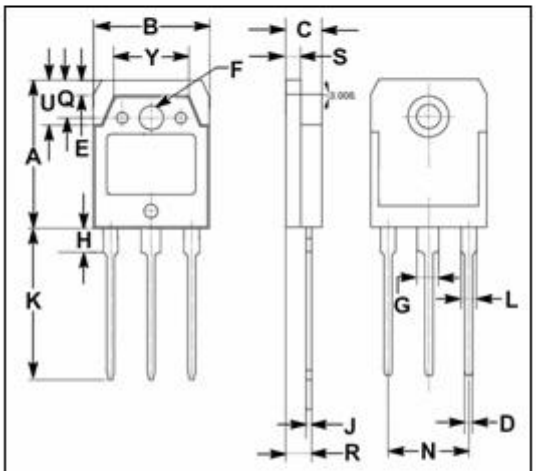
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 450V(Min)
- High DC Current Gain
  : h_{FE}= 500(Min) @ I_C= 5A, V_{CE}= 3V
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio frequency power amplifier and low speed high current switching industrial applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	20	A
P_C	Collector Power Dissipation @T_a=25℃	3	W
	Collector Power Dissipation @T_C=25℃	100	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA, I_B= 0	450			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 20mA ,I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A, I_B= 8mA			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A, I_B= 8mA			2.0	V
I_{CBO}	Collector Cutoff current	V_{CB}= 500V, I_E= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C= 0			20	mA
h_{FE}	DC Current Gain	I_C= 5A; V_{CE}= 3V	500			
Switching Times						
t_{on}	Turn-On Time	I_C = 5A,I_{B1} = I_{B2}= 8mA		1.5		μs
t_{stg}	Storage Time			7.0		μs
t_f	Fall Time			4.0		μs